

34. (Twice Amended) A semiconductor device comprising:

a semiconductor substrate;

a first insulating film formed on said semiconductor substrate;

a first conductor formed on said semiconductor substrate through said first insulating film;

a first upper wire formed on said first insulating film and said first conductor; and

a second insulating film formed on said first upper wire and over said first insulating film, said second insulating film including a thin area over said first conductor for guiding a laser beam;

a second conductor formed on said semiconductor substrate through said first insulating film below the thin area; and

a second upper wire formed on an extension line of said first upper wire on said first insulating film and said second conductor beneath said second insulating film.

35. (Amended) A semiconductor device comprising:

a semiconductor substrate;

a first insulating film formed on said semiconductor substrate;

a first conductor formed on said semiconductor substrate through said first insulating film, including a first portion formed on said semiconductor substrate and a second portion formed on the first portion made of a different material from that of the first portion;

a first upper wire formed on said first insulating film and said first conductor; and

FINNEGAN
HENDERSON
FARABOW
GARRETT &
DUNNER LLP

1300 I Street, NW
Washington, DC 20005
202.408.4000
Fax 202.408.4400
www.finnegan.com